

Phase leg

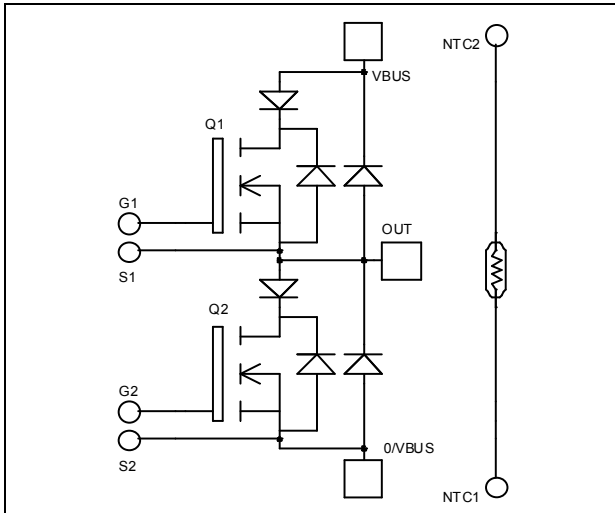
Series & parallel diodes

MOSFET Power Module

$V_{DSS} = 500V$

$R_{DSon} = 38m\Omega \text{ typ @ } T_j = 25^\circ C$

$I_D = 90A \text{ @ } T_c = 25^\circ C$

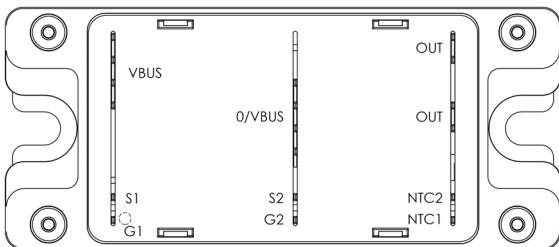


Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	90
		$T_c = 80^\circ C$	67
I_{DM}	Pulsed Drain current	360	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	45	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	694
I_{AR}	Avalanche current (repetitive and non repetitive)	46	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 500V			200	μA
		V _{GS} = 0V, V _{DS} = 400V			1000	
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 45A		38	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 5mA	3		5	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±30 V, V _{DS} = 0V			±200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance	V _{GS} = 0V		11.2		nF
C _{oss}	Output Capacitance	V _{DS} = 25V		2.4		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		0.18		
Q _g	Total gate Charge	V _{GS} = 10V		246		nC
Q _{gs}	Gate – Source Charge	V _{Bus} = 250V		66		
Q _{gd}	Gate – Drain Charge	I _D = 90A		130		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		18		ns
T _r	Rise Time	V _{GS} = 15V		35		
T _{d(off)}	Turn-off Delay Time	V _{Bus} = 333V		87		
T _f	Fall Time	I _D = 90A R _G = 2Ω		77		
E _{on}	Turn-on Switching Energy	Inductive switching @ 25°C		1510		μJ
E _{off}	Turn-off Switching Energy	V _{GS} = 15V, V _{Bus} = 333V I _D = 90A, R _G = 2Ω		1452		
E _{on}	Turn-on Switching Energy	Inductive switching @ 125°C		2482		μJ
E _{off}	Turn-off Switching Energy	V _{GS} = 15V, V _{Bus} = 333V I _D = 90A, R _G = 2Ω		1692		
R _{thJC}	Junction to Case Thermal Resistance				0.18	°C/W

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V			250	μA
I _F	DC Forward Current	T _c = 80°C		90		A
V _F	Diode Forward Voltage	I _F = 90A		1.6	1.8	V
		I _F = 180A		1.9		
		I _F = 90A	T _j = 125°C	1.4		
t _{rr}	Reverse Recovery Time	I _F = 90A V _R = 400V	T _j = 25°C	85		ns
			T _j = 125°C	160		
Q _{rr}	Reverse Recovery Charge	di/dt = 600A/μs	T _j = 25°C	390		nC
			T _j = 125°C	2100		
R _{thJC}	Junction to Case Thermal Resistance				0.45	°C/W

Parallel diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V				250	μA
I _F	DC Forward Current		T _c = 90°C		90		A
V _F	Diode Forward Voltage	I _F = 90A			1.8	2.2	V
		I _F = 180A			2		
		I _F = 90A	T _j = 125°C		1.3		
t _{rr}	Reverse Recovery Time	I _F = 90A V _R = 400V di/dt = 600A/μs	T _j = 25°C		25		ns
			T _j = 125°C		160		
Q _{rr}	Reverse Recovery Charge	I _F = 90A V _R = 400V di/dt = 600A/μs	T _j = 25°C		105		nC
			T _j = 125°C		1440		
R _{thJC}	Junction to Case Thermal Resistance					0.45	°C/W

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Max</i>	<i>Unit</i>		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	150	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	100			
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

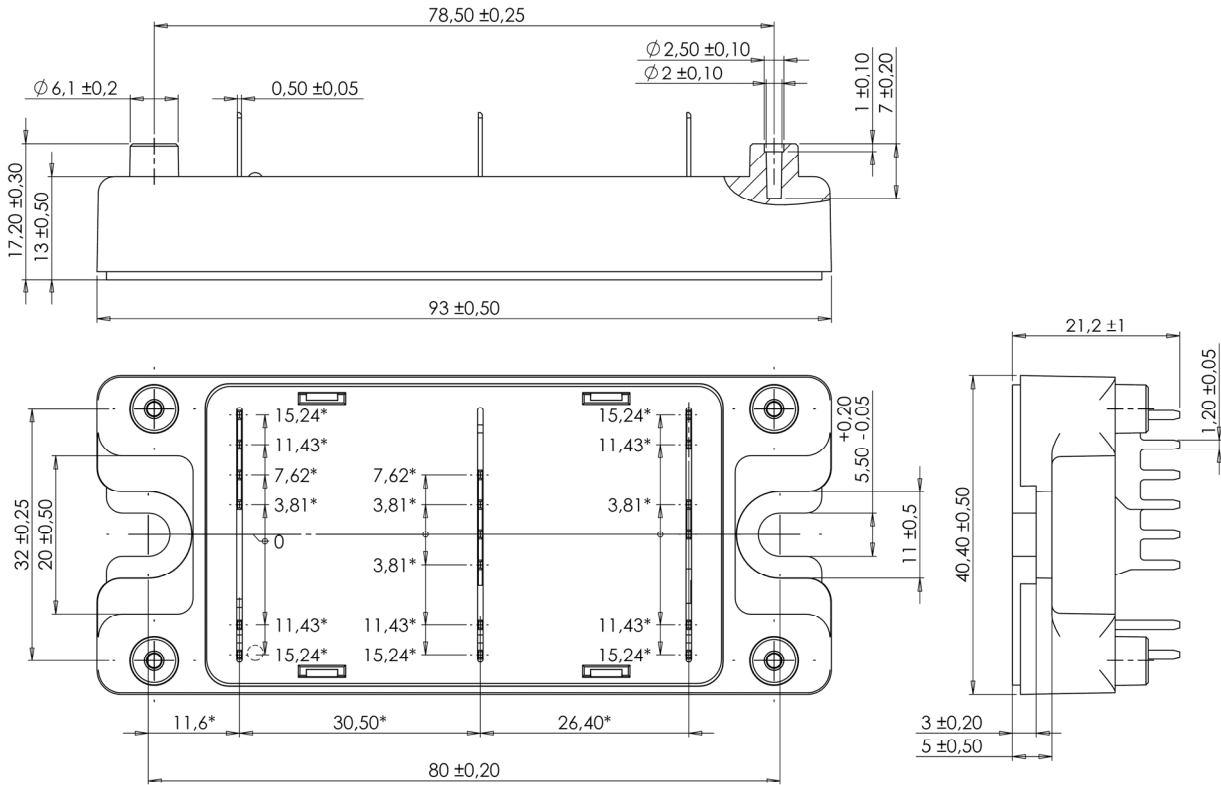
Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B		T _C =100°C	4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

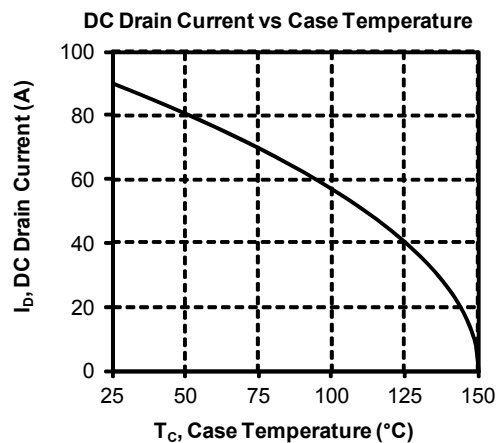
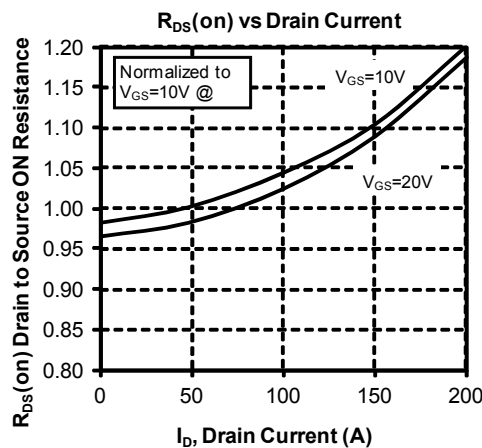
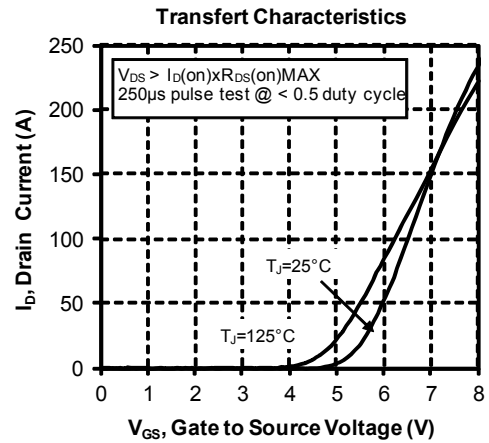
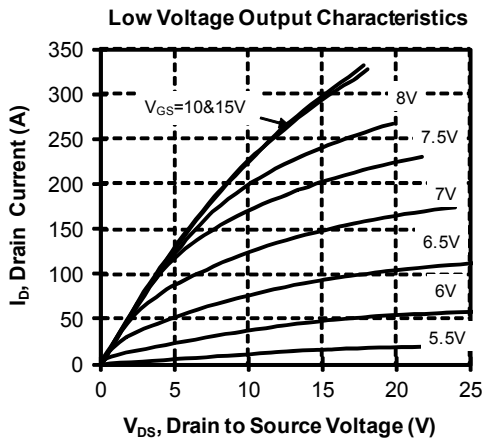
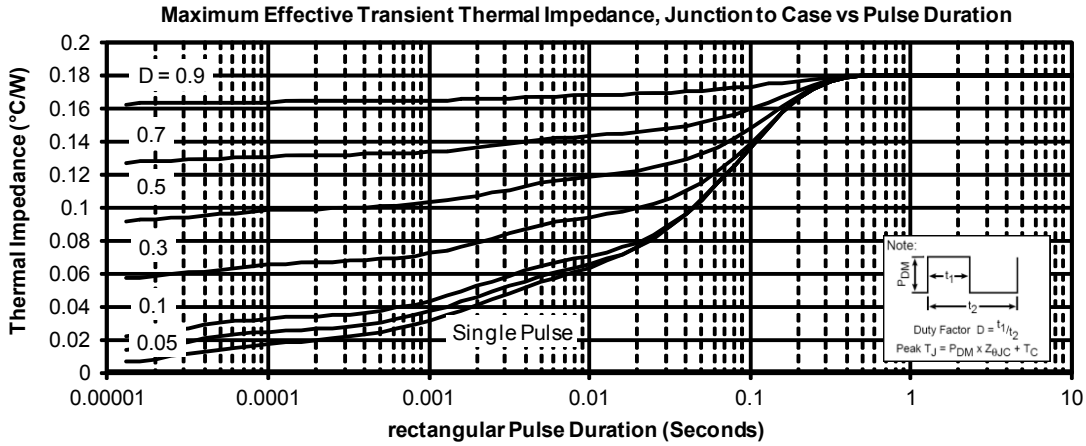
SP4 Package outline (dimensions in mm)

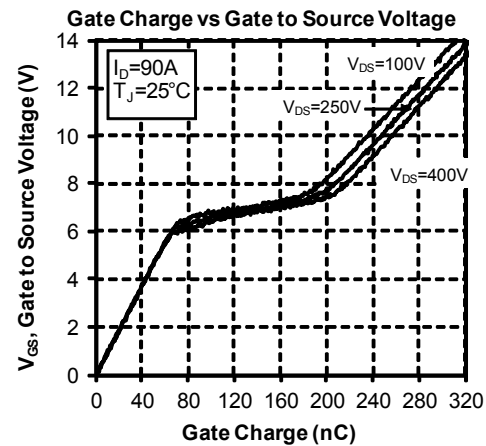
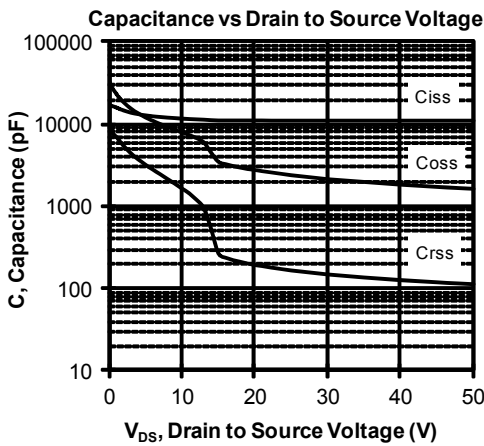
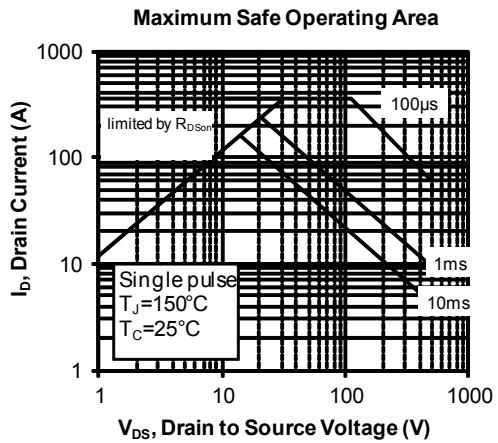
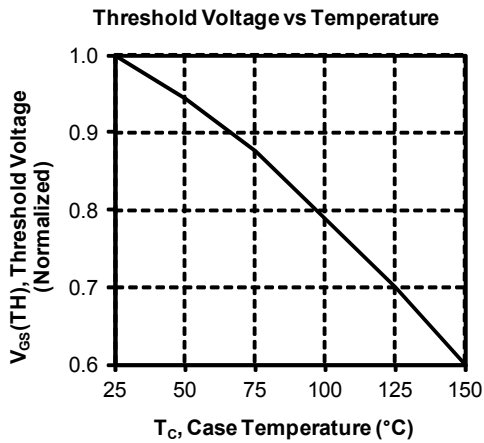
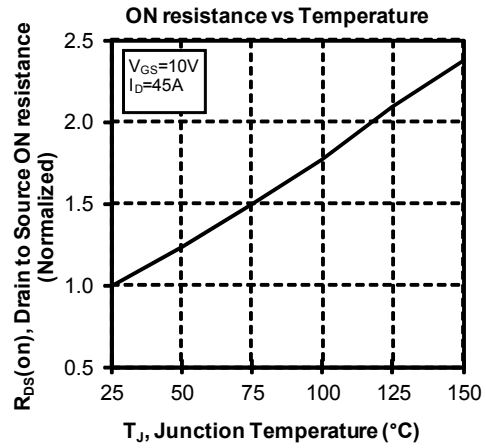
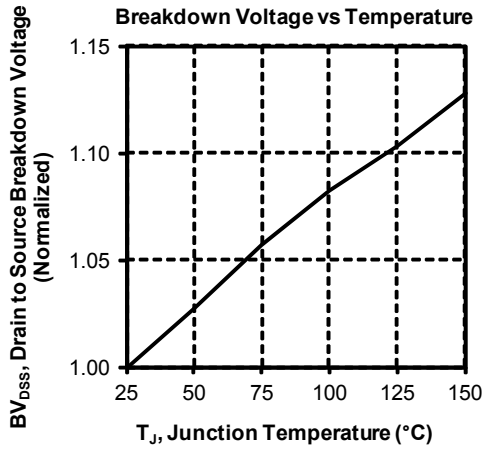


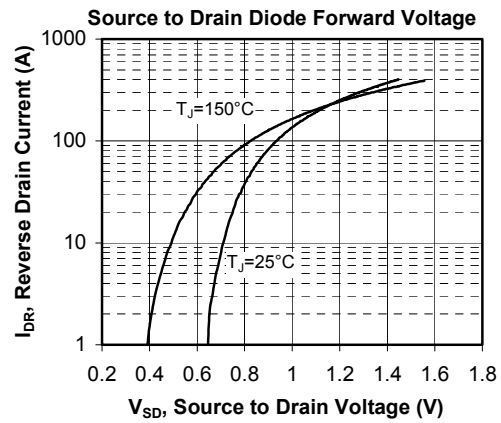
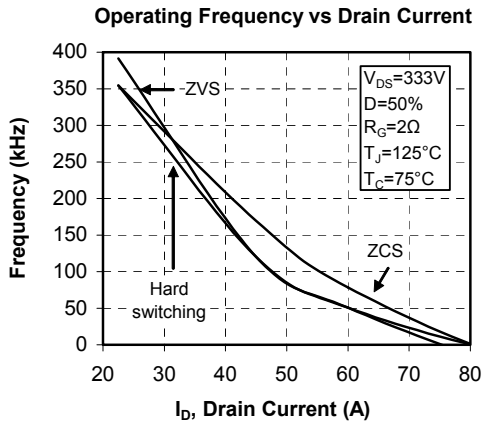
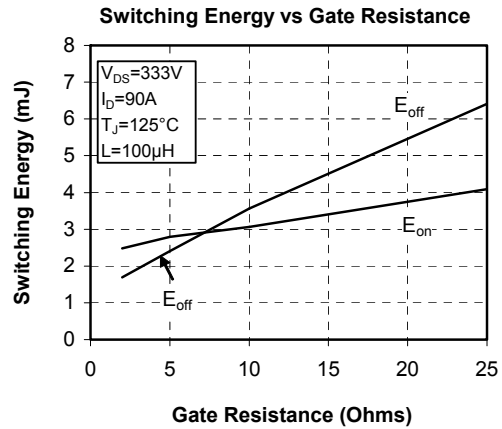
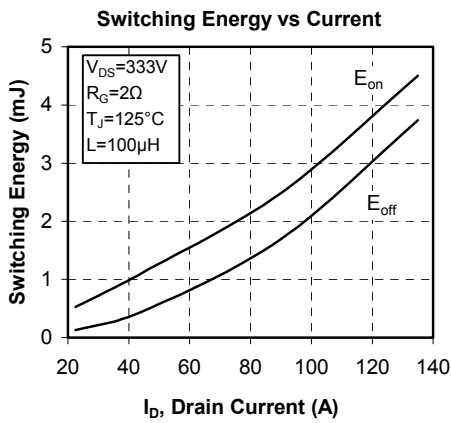
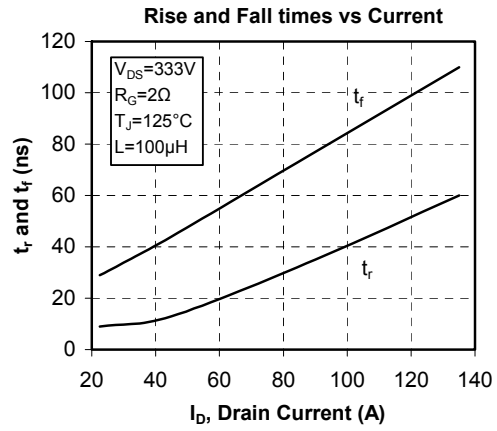
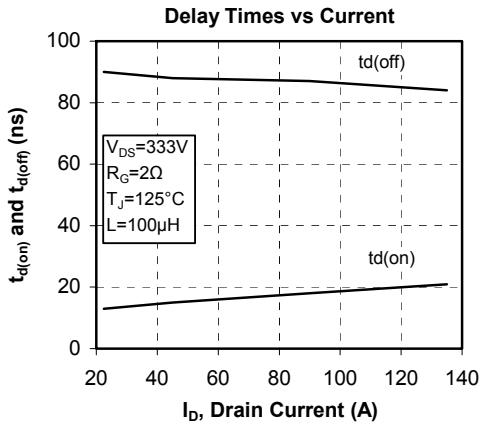
ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS $\pm \phi 1$

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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